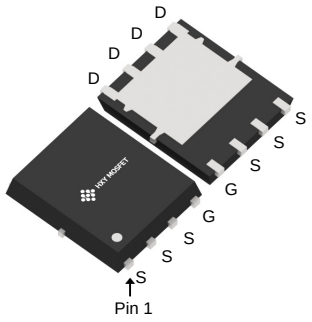
HAONS32304

N-Channel Enhancement Mode MOSFET

Description

The HAONS32304 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

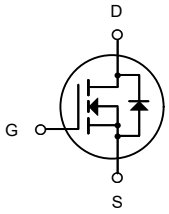


DFN5X6-8L

General Features

V_{DS} = 30V I_D = 150A

$R_{DS(ON)}$ < 2.4mΩ V_{GS}=10V



N-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HAONS32304	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings (T_C=25 °C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V	150	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V	106	A
I_{DM}	Pulsed Drain Current	450	A
EAS	Single Pulse Avalanche Energy	625	mJ
I_{AS}	Avalanche Current	---	A
P_D@T_C=25℃	Total Power Dissipation	150	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case	1.6	℃/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=17A	---	1.5	2	mΩ
		V_{GS}=4.5V , I_D=17A	---	2.3	3	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1	---	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=30V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=30V, V_{GS}=0V , T_J=100℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=17A	---	46	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.88	---	Ω
Q_g	Total Gate Charge	V_{DS}=15V , V_{GS}=10V , I_D=17A	---	105	---	nC
Q_{gs}	Gate-Source Charge		---	20	---	
Q_{gd}	Gate-Drain Charge		---	20	---	
$T_{d(on)}$	Turn-On Delay Time	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω	---	13	---	ns
T_r	Rise Time		---	30	---	
$T_{d(off)}$	Turn-Off Delay Time		---	85	---	
T_f	Fall Time		---	50	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , f=1MHz	---	6040	---	pF
C_{oss}	Output Capacitance		---	627	---	
C_{rss}	Reverse Transfer Capacitance		---	551	---	
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	150	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=17A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=17A , di/dt=100A/μs , T_J=25℃	---	28	---	nS
Q_{rr}	Reverse Recovery Charge		---	16	---	nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=30V,V_G=10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Characteristics

Figure 1. Output Characteristics

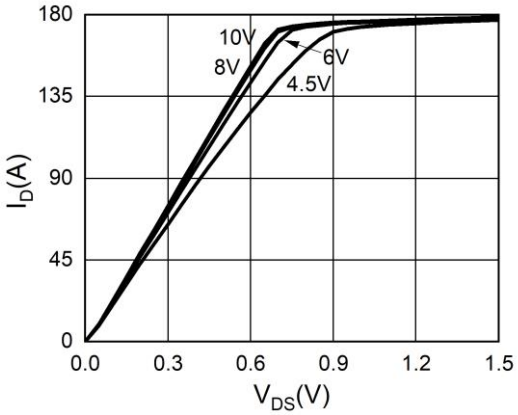


Figure 2. Transfer Characteristics

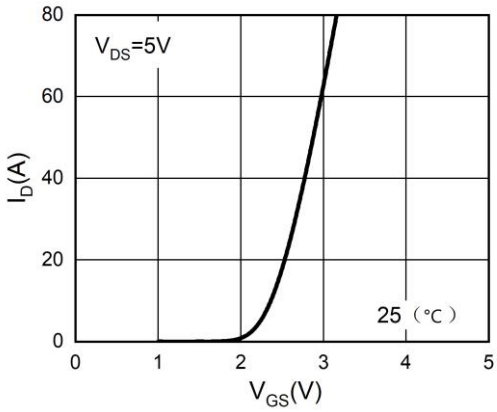


Figure 3. Power Dissipation

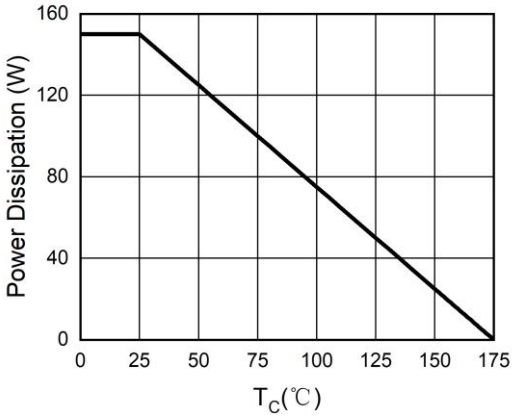


Figure 4. Drain Current

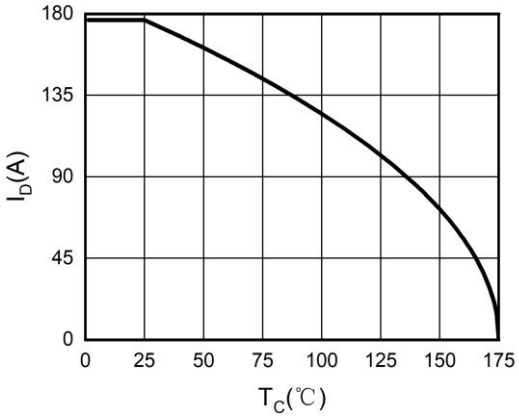


Figure 5. BV_{DSS} vs Junction Temperature

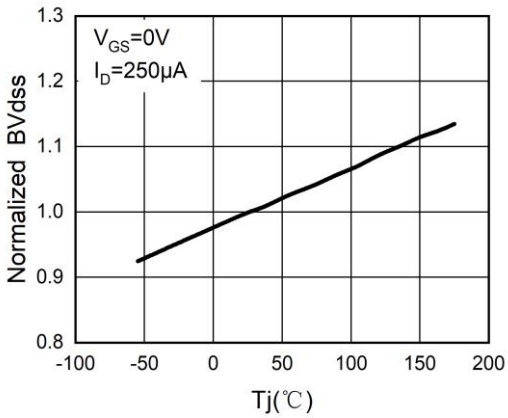


Figure 6. $R_{DS(ON)}$ vs Junction Temperature

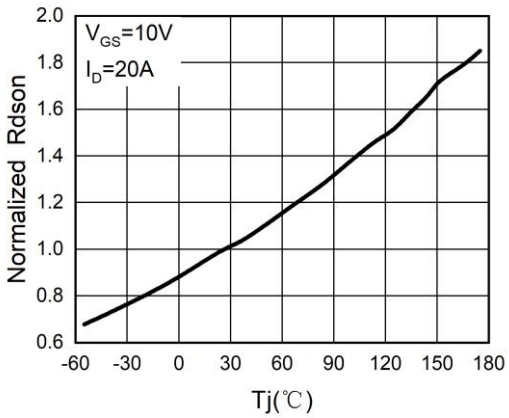


Figure 7. Gate Charge Waveforms

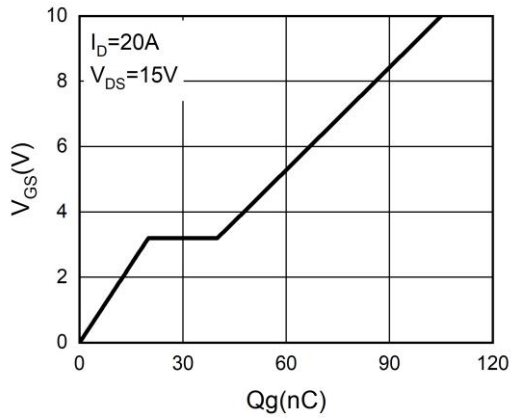


Figure 8. Capacitance

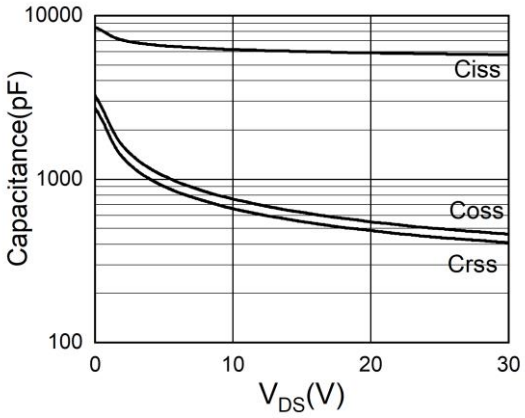


Figure 9. Body-Diode Characteristics

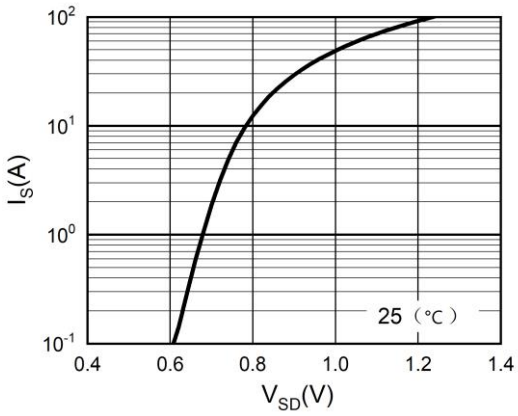
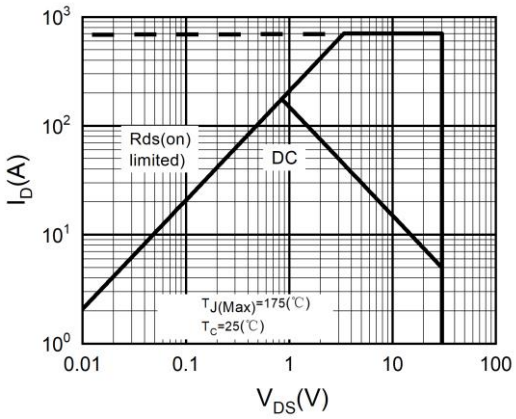


Figure 10. Maximum Safe Operating Area



Test Circuit

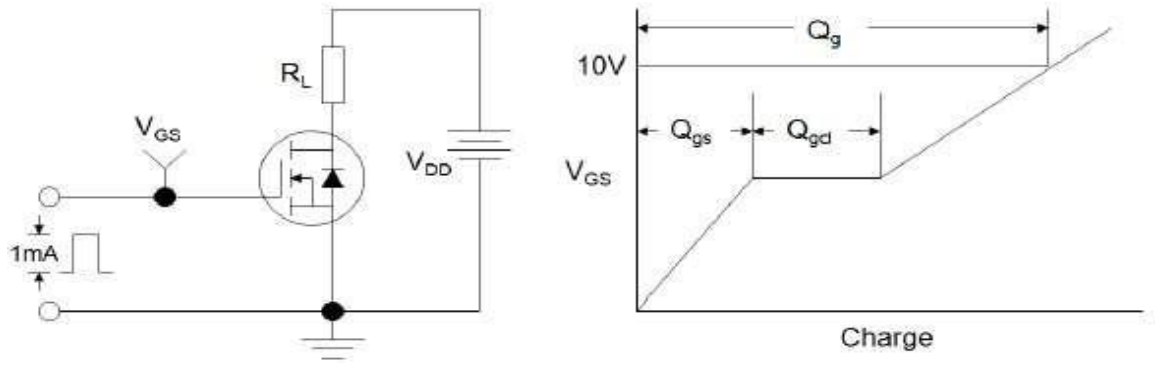


Figure1:Gate Charge Test Circuit & Waveform

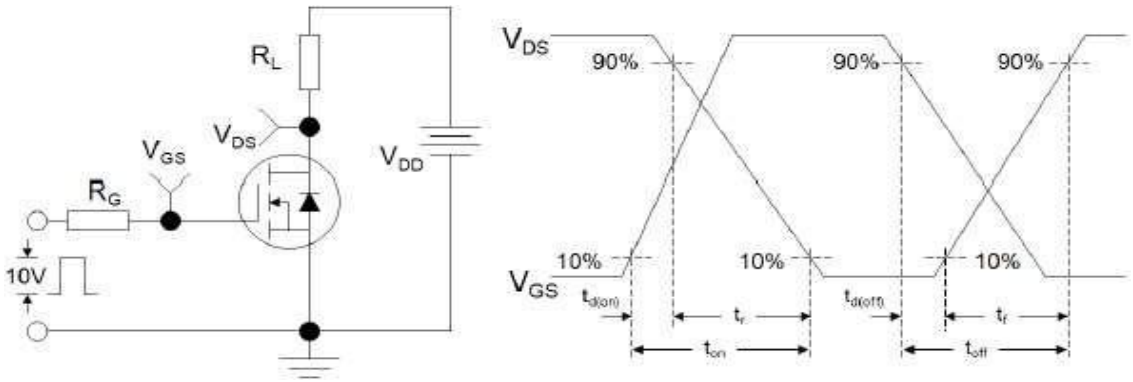


Figure 2: Resistive Switching Test Circuit & Waveforms

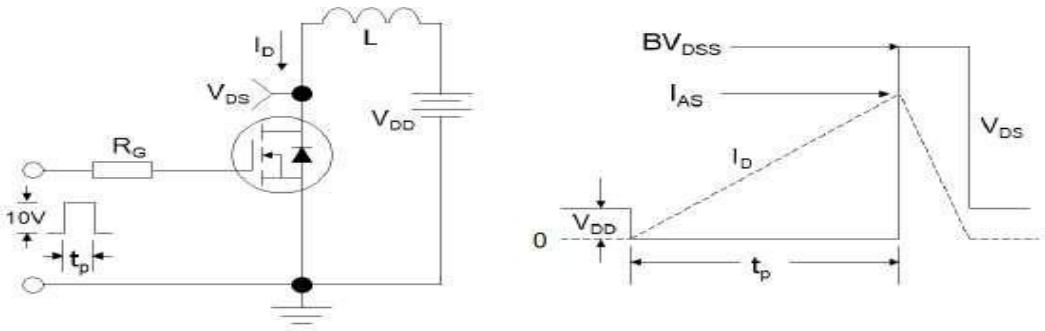
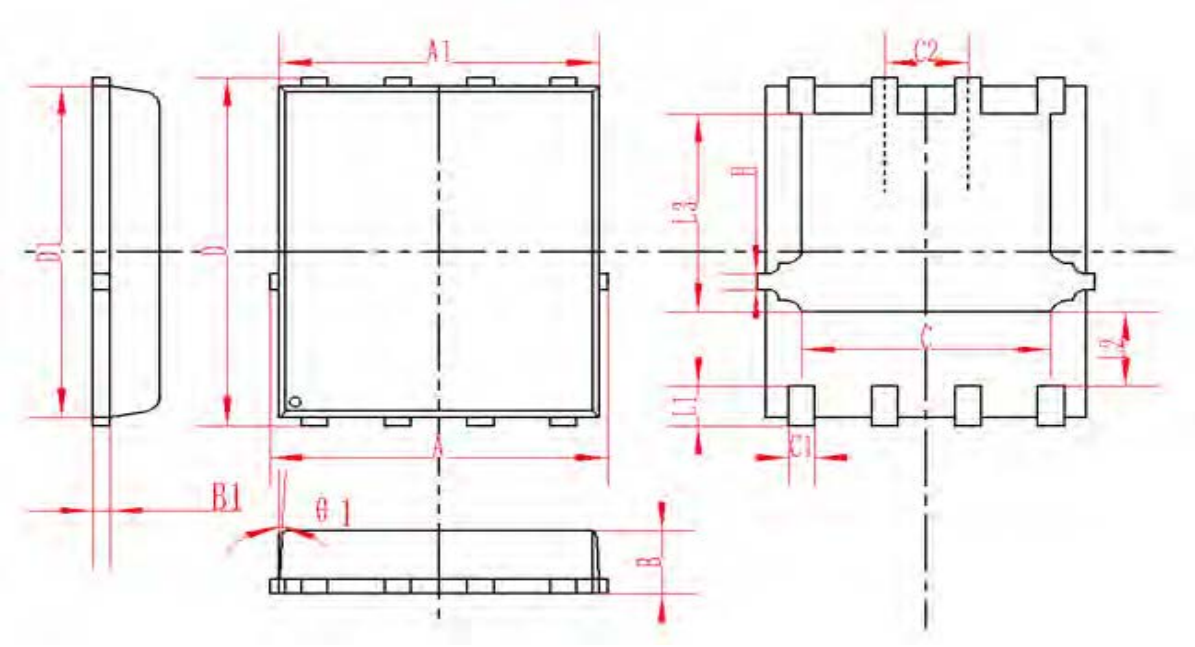


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010

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